

MOSFETs Silicon N-Channel MOS (DTMOSIV)

# **TK31J60W**

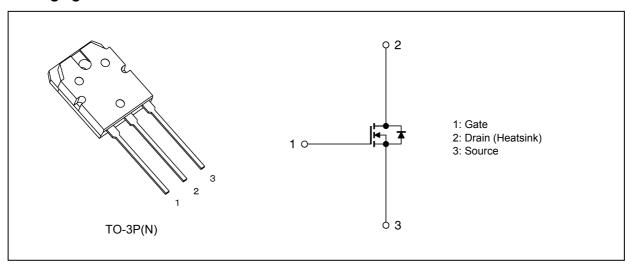
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)}$  = 0.073  $\Omega$  (typ.) by used to Super Junction Structure: DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th} = 2.7$  to 3.7 V ( $V_{DS} = 10$  V,  $I_D = 1.5$  mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                          |                | Symbol           | Rating     | Unit  |
|--|----------------|------------------|------------|-------|
| Drain-source voltage                     |                | $V_{DSS}$        | 600        | V     |
| Gate-source voltage                      |                | V <sub>GSS</sub> | ±30        |       |
| Drain current (DC)                       | (Note 1)       | I <sub>D</sub>   | 30.8       | Α     |
| Drain current (pulsed)                   | (Note 1)       | I <sub>DP</sub>  | 123        |       |
| Power dissipation (T <sub>c</sub> = 25°C | <del>(</del> ) | $P_{D}$          | 230        | W     |
| Single-pulse avalanche energy            | (Note 2)       | E <sub>AS</sub>  | 437        | mJ    |
| Avalanche current                        |                | I <sub>AR</sub>  | 7.7        | Α     |
| Reverse drain current (DC)               | (Note 1)       | I <sub>DR</sub>  | 30.8       | ]     |
| Reverse drain current (pulsed)           | (Note 1)       | I <sub>DRP</sub> | 123        |       |
| Channel temperature                      |                | T <sub>ch</sub>  | 150        | °C    |
| Storage temperature                      |                | T <sub>stg</sub> | -55 to 150 | ]     |
| Mounting torque                          |                | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 0.543 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 12.9 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 7.7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



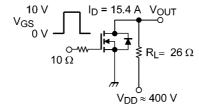
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min | Тур.  | Max   | Unit |
|--------------------------------|----------------------|---|-----|-------|-------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _   | _     | ±1    | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V    | _   | _     | 10    |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 600 | _     | _     | V    |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.5 mA   | 2.7 | _     | 3.7   |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15.4 A   | _   | 0.073 | 0.088 | Ω    |

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz | _   | 3000 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub>   |   | _   | 9.5  | _   |      |
| Output capacitance             | C <sub>oss</sub>   |   | _   | 70   | _   |      |
| Effective output capacitance   | C <sub>o(er)</sub> | V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V         | _   | 123  | _   |      |
| Gate resistance                | r <sub>g</sub>     | V <sub>DS</sub> = OPEN, f = 1 MHz                           | _   | 2    | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>     | See Figure 6.2.1  | _   | 32   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>    |   | _   | 70   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>     |   | _   | 8.5  | _   |      |
| Switching time (turn-off time) | t <sub>off</sub>   |   | _   | 165  | _   |      |
| MOSFET dv/dt ruggedness        | dv/dt              | V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 7.7 A        | 50  | _    | _   | V/ns |



 $Duty \leq 1\%, \ t_W = 10 \ \mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30.8 \text{ A}$ | _   | 86   |     | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |   |     | 18   |     |      |
| Gate-drain charge                               | $Q_{gd}$         |   | _   | 41   |     |      |

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics               | Symbol          | Test Condition   | Min | Тур. | Max  | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage         | $V_{DSF}$       | I <sub>DR</sub> = 30.8 A, V <sub>GS</sub> = 0 V                          | _   |      | -1.7 | V    |
| Reverse recovery time         | t <sub>rr</sub> | I <sub>DR</sub> = 15.4 A, V <sub>GS</sub> = 0 V                          | _   | 410  | _    | ns   |
| Reverse recovery charge       | $Q_{rr}$        | -dI <sub>DR</sub> /dt = 50 A/μs  |     | 3.5  | _    | μС   |
| Peak reverse recovery current | I <sub>rr</sub> |  |     | 17   | _    | Α    |
| Diode dv/dt ruggedness        | dv/dt           | I <sub>DR</sub> = 15.4 A, V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 400 V | 15  | _    | _    | V/ns |



### 7. Marking (Note)

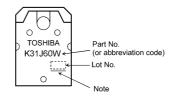


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

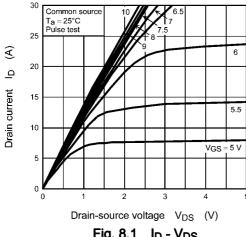
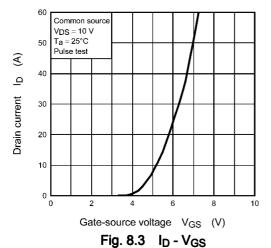


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Drain-source voltage V<sub>DSS</sub> 580 540

Common source VGS = 0 V ID = 10 mA Pulse test

 $\widehat{\mathbf{S}}$ 

660

620

Ambient temperature T<sub>a</sub> (°C) Fig. 8.5 V<sub>DSS</sub> - T<sub>a</sub>

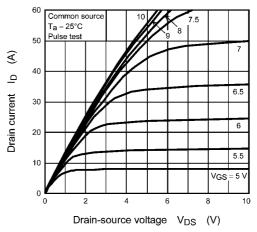


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

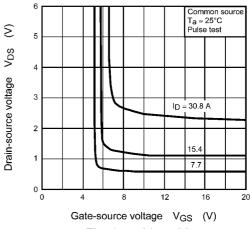


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

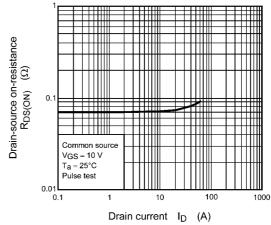


Fig. 8.6  $R_{DS(ON)}$  -  $I_D$ 

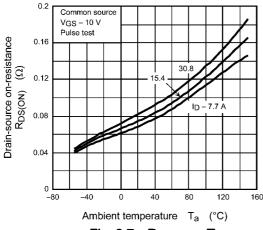
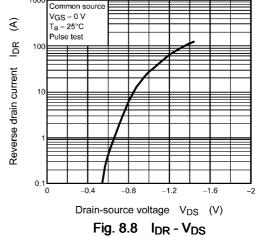


Fig. 8.7  $R_{DS(ON)}$  -  $T_a$ 



15

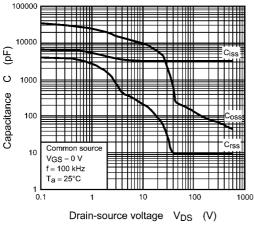


Fig. 8.9 C - V<sub>DS</sub>

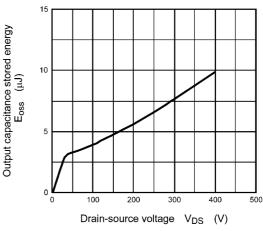


Fig. 8.10 E<sub>OSS</sub> - V<sub>DS</sub>

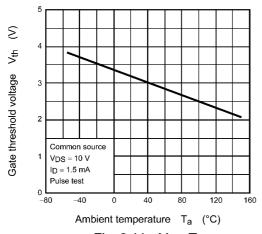


Fig. 8.11  $V_{th}$  -  $T_a$ 

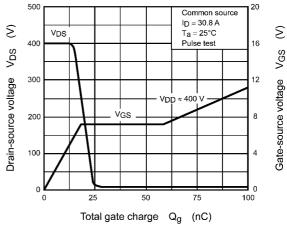


Fig. 8.12 Dynamic Input/Output Characteristics

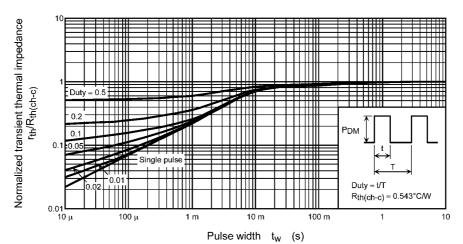


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

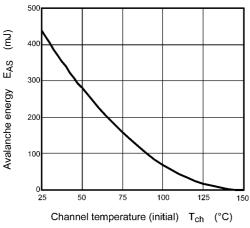


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

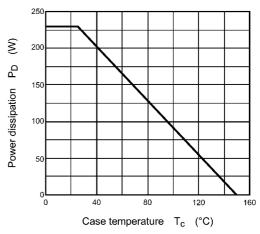


Fig. 8.15 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

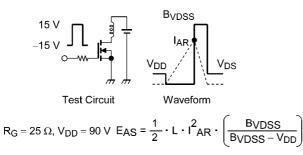


Fig. 8.16 Test Circuit/Waveform

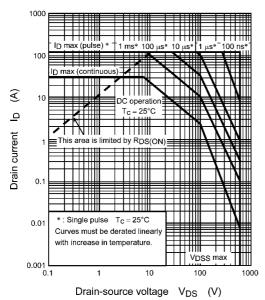


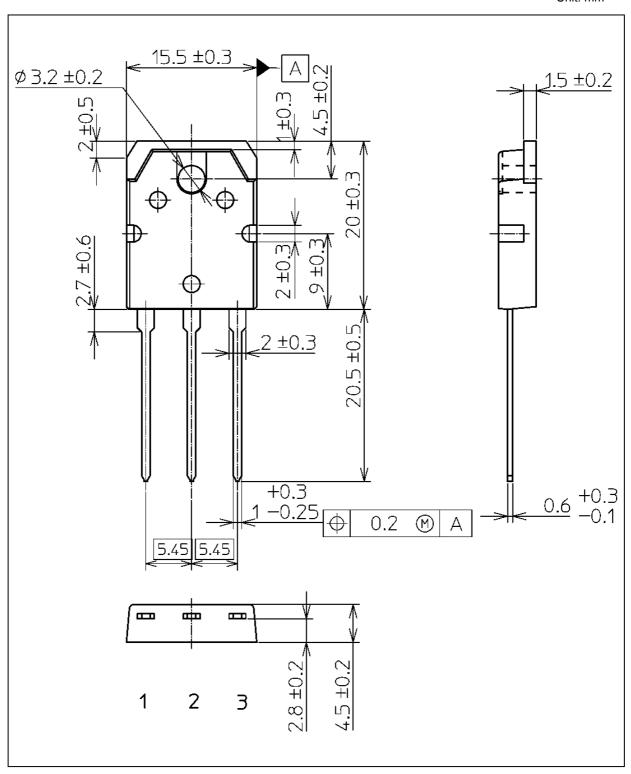
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 4.6 g (typ.)

|                    | Package Name(s) |
|--------------------|-----------------|
| JEITA: SC-65       |                 |
| TOSHIBA: 2-16C1S   |                 |
| Nickname: TO-3P(N) |                 |



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